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INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		APPLICANT(S) Seong-Ju PARK et al.				
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U.S. PATENT DOCUMENTS						
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)						
TYT	1.	"Tetsuya Yamamoto et al.; "Solution Using a Codoping Method to Unipolarity for the Fabrication of p-Type ZnO"; Jpn. J. Appl. Phys.; Vol. 38, Part 2, No. 2B; February 15 1999; pp L166-L169				
TYT	2.	Mathew Joseph et al.; "p-Type Electrical Conduction in ZnO Thin Films by Ga and N Codoping"; Jpn. J. Appl. Phys.; Vol. 38, Part 2, No. 11A; November 1, 1999; pp L1205-L1207				
TYT	3.	Toru Aoki et al.; "ZnO diode fabricated by excimer-laser doping"; Applied Physics Letters; Vol. 76, No. 22; May 29, 2000; pp 3257-3258				
TYT	4.	Y. R. Ryu et al.; "Synthesis of p-type ZnO films"; Journal of Crystal Growth; 2000; pp 330-334				
TYT	5.	D.C. Look et al.; "Characterization of homoepitaxial p-type ZnO grown by molecular beam epitaxy"; Applied Physics Letters; Vol 81, No. 10; September 2, 2002; pp 1830-1832				
EXAMINER THANH TRAN				DATE CONSIDERED 10/7/04		
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